

ABSTRACT OF THE DISCLOSURE

A semiconductor memory device has a plurality of memory cells each having a first ferroelectric capacitor for storing data as a polarization value. First voltage applying means applies a first read voltage between the pair of electrodes of the first ferroelectric capacitor composing that one of the plurality of memory cells from which data is to be read. Data reading means detects the polarization value in the first ferroelectric capacitor when the first read voltage is applied between the pair of electrodes of the first ferroelectric capacitor and thereby reads the data stored in the first ferroelectric capacitor therefrom. A hysteresis loop in the first ferroelectric capacitor is shifted in a direction of voltage opposite in polarity to the first read voltage.